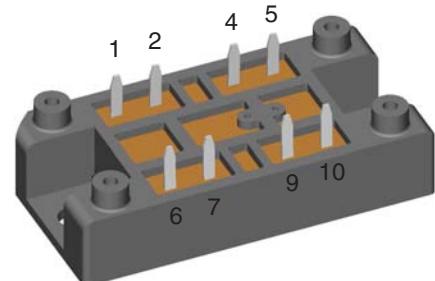
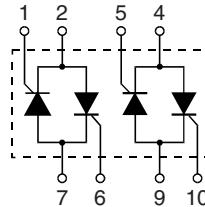


AC Controller Modules

I_{RMS} = 2x 45 A
V_{RRM} = 1200-1600 V

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Type
V	V	
1200	1200	VW2x45-12io1
1400	1400	VW2x45-14io1
1600	1600	VW2x45-16io1



Symbol	Conditions	Maximum Ratings		
I _{RMS}	T _C = 85°C; (per phase)	45	A	
I _{TRMS}	T _{VJ} = T _{VJM}	32	A	
I _{TAVM}	T _C = 85°C; (180° sine ; per thyristor)	20	A	
I _{TSM}	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	300	A	
	V _R = 0 t = 8.3 ms (60 Hz), sine	320	A	
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine	270	A	
	V _R = 0 t = 8.3 ms (60 Hz), sine	290	A	
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	450	A ² s	
	V _R = 0 t = 8.3 ms (60 Hz), sine	430	A ² s	
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine	360	A ² s	
	V _R = 0 t = 8.3 ms (60 Hz), sine	350	A ² s	
(di/dt) _{cr}	T _{VJ} = T _{VJM} repetitive, I _T = 45 A	100	A/μs	
	f = 50 Hz, t _p = 200 μs			
	V _D = 2/3 V _{DRM}			
	I _G = 0.45 A non repetitive, I _T = I _{TAVM}	500	A/μs	
	di _G /dt = 0.45 A/μs			
(dv/dt) _{cr}	T _{VJ} = T _{VJM} V _{DR} = 2/3 V _{DRM}	1000	V/μs	
	R _{GR} = ∞; method 1 (linear voltage rise)			
P _{GM}	T _{VJ} = T _{VJM} t _p = 30 μs	10	W	
	I _T = I _{TAVM} t _p = 300 μs	5	W	
P _{GAVM}		0.5	W	
V _{RGM}		10	V	
T _{VJ}		-40...+125	°C	
T _{VJM}		125	°C	
T _{stg}		-40...+125	°C	
V _{ISOL}	50/60 Hz, RMS t = 1 min	3000	V~	
	I _{ISOL} ≤ 1 mA t = 1 s	3600	V~	
M _d	Mounting torque (M5)	2-2.5/18-22	Nm/lb.in.	
Weight	typ.	35	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5	mA
V_T	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.52	V
V_{TO}	For power-loss calculations only	0.85	V	
r_T		15	mΩ	
V_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	\leq	1.5 V
		$T_{VJ} = -40^\circ\text{C}$	\leq	1.6 V
I_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	\leq	100 mA
		$T_{VJ} = -40^\circ\text{C}$	\leq	200 mA
V_{GD}	$T_{VJ} = T_{VJM}$	$V_D = \frac{2}{3}V_{DRM}$	\leq	0.2 V
I_{GD}			\leq	5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$	\leq	450	mA
	$I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$			
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2}V_{DRM}$	\leq	2	μs
	$I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$			
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$	typ.	150	μs
	$V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = \frac{2}{3}V_{DRM}$			
R_{thJC}	per thyristor; DC		1.25	K/W
	per module		0.31	K/W
R_{thJK}	per thyristor; DC		1.55	K/W
	per module		0.39	K/W
d_s	Creeping distance on surface		12.7	mm
d_A	Creepage distance in air		9.4	mm
a	Max. allowable acceleration		50	m/s ²

Dimensions in mm (1 mm = 0.0394")

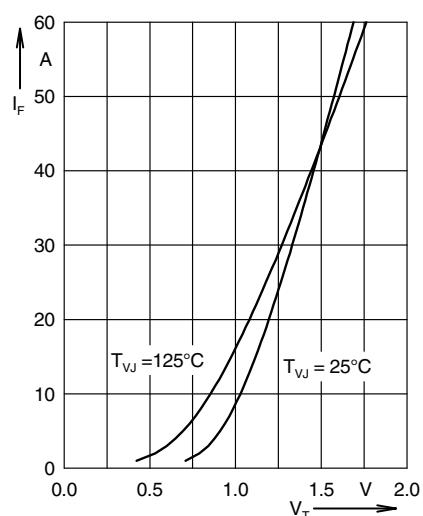
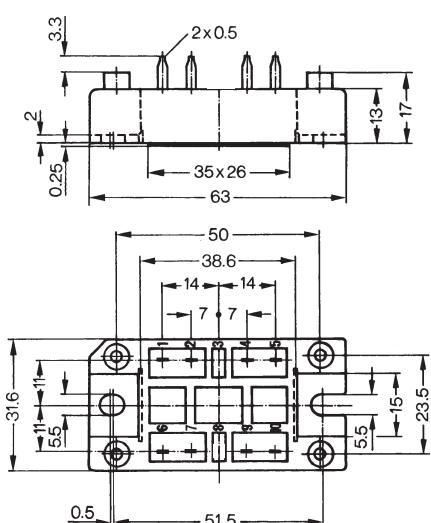


Fig. 3 Forward current vs. voltage drop per leg

IXYS reserves the right to change limits, test conditions and dimensions

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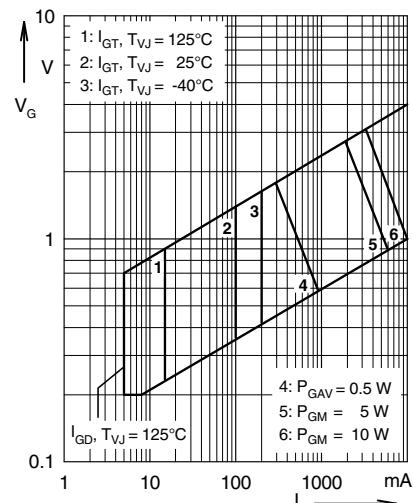


Fig. 1 Gate trigger characteristics

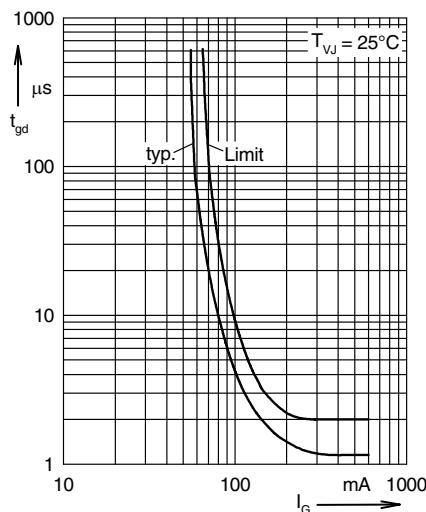


Fig. 2 Gate trigger delay time

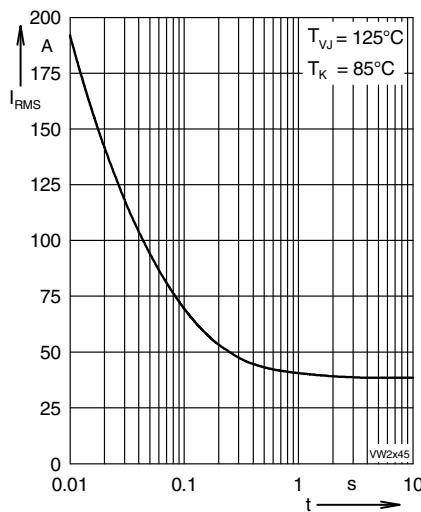


Fig. 4 Rated RMS current vs. time (360° conduction)

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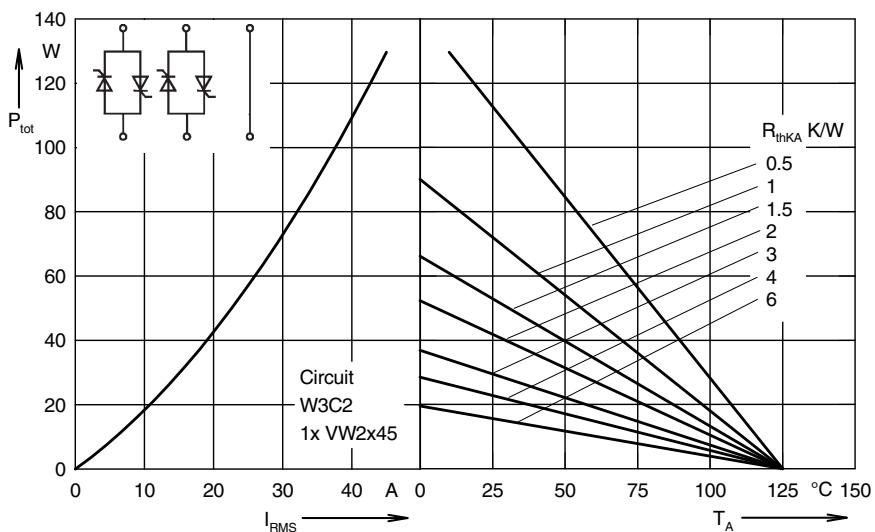


Fig. 5 Load current capability for two phase AC controller

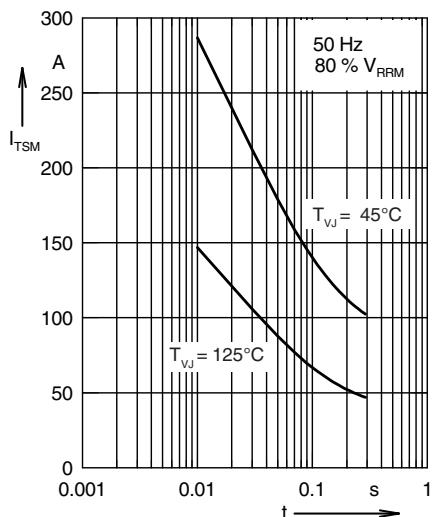


Fig. 6 Surge overload current

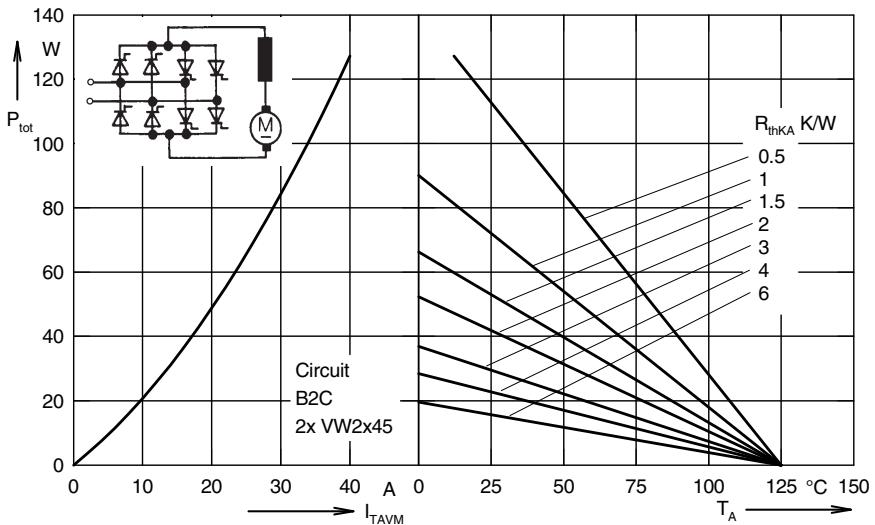


Fig. 7 Power dissipation vs. direct output current and ambient temperature cyclo converter, four quadrant operation

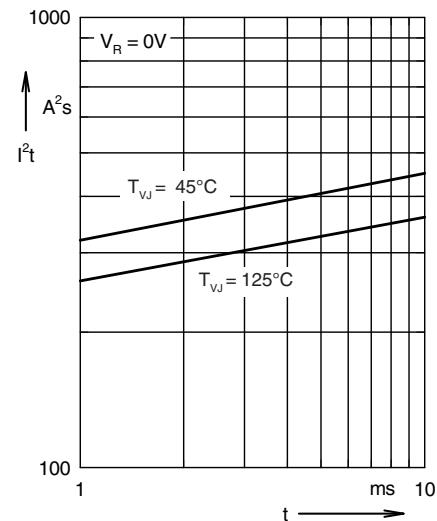


Fig. 8 I^2t vs. time (per thyristor)

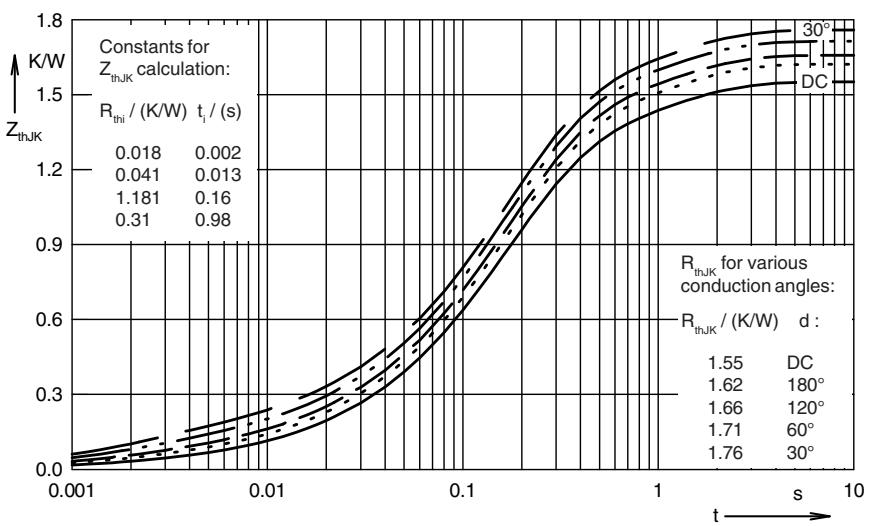


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

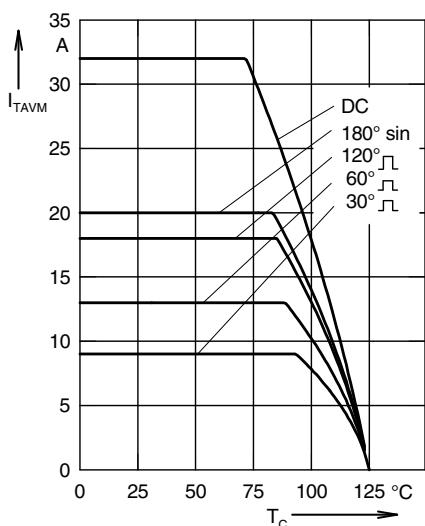


Fig. 10 Maximum forward current at case temperature
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